

/ Descriptions

SOT-23 NPN Silicon NPN transistor in a SOT-23 Plastic Package.

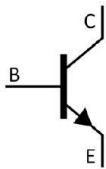
/ Features

High power gain, low noise figure, very low intermodulation distortion.

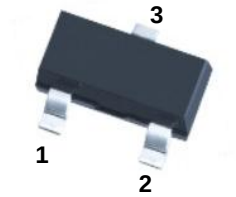
/ Applications

RF wideband amplifiers and oscillators.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

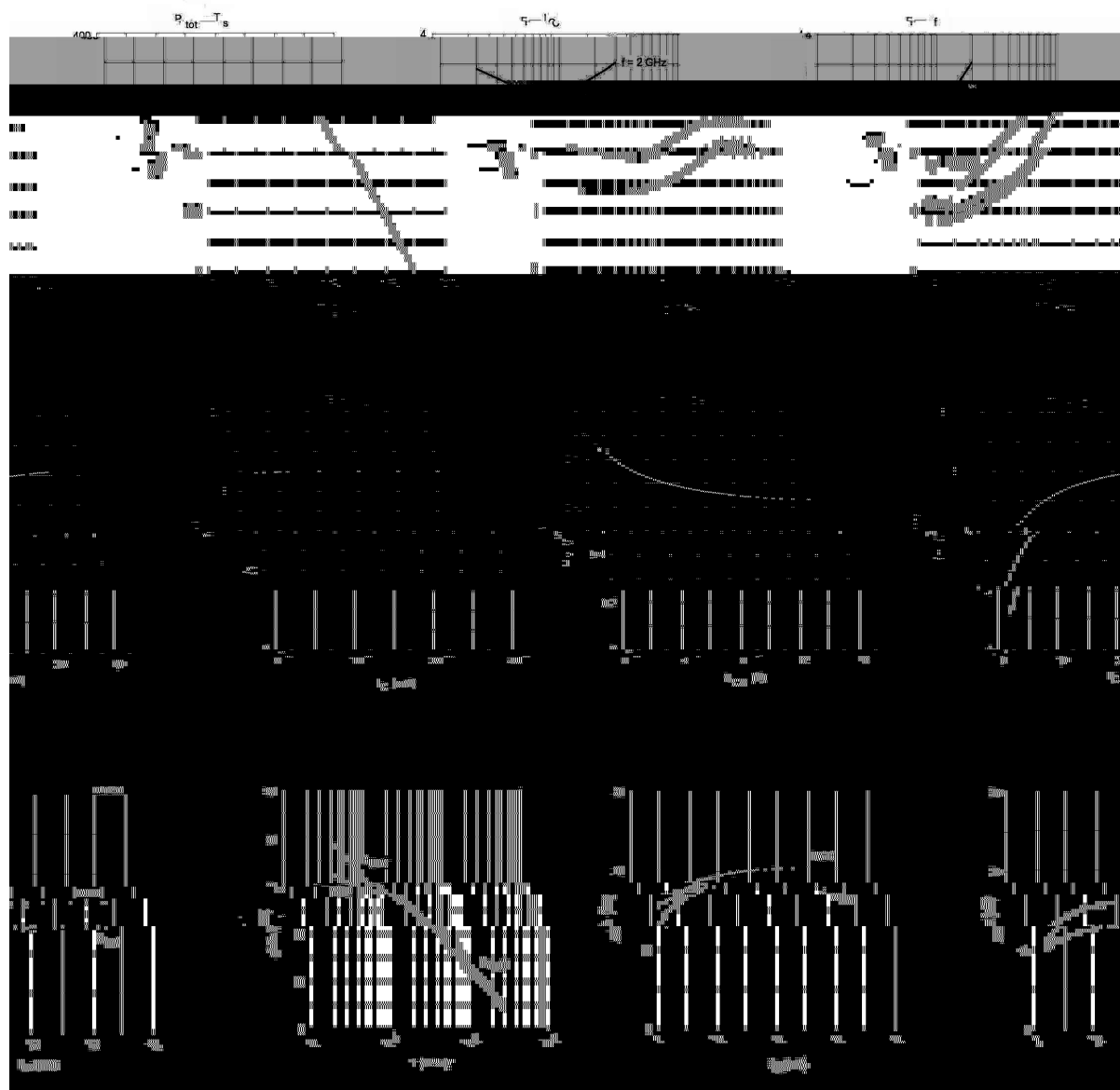
/ Marking

h_{FE} Range	>40
Marking	HR2P

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	15	V
Collector to Emitter Voltage	V_{CEO}	12	V
Emitter to Base Voltage	V_{EBO}	2.0	V
Collector Current - Continuous	I_C	35	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min
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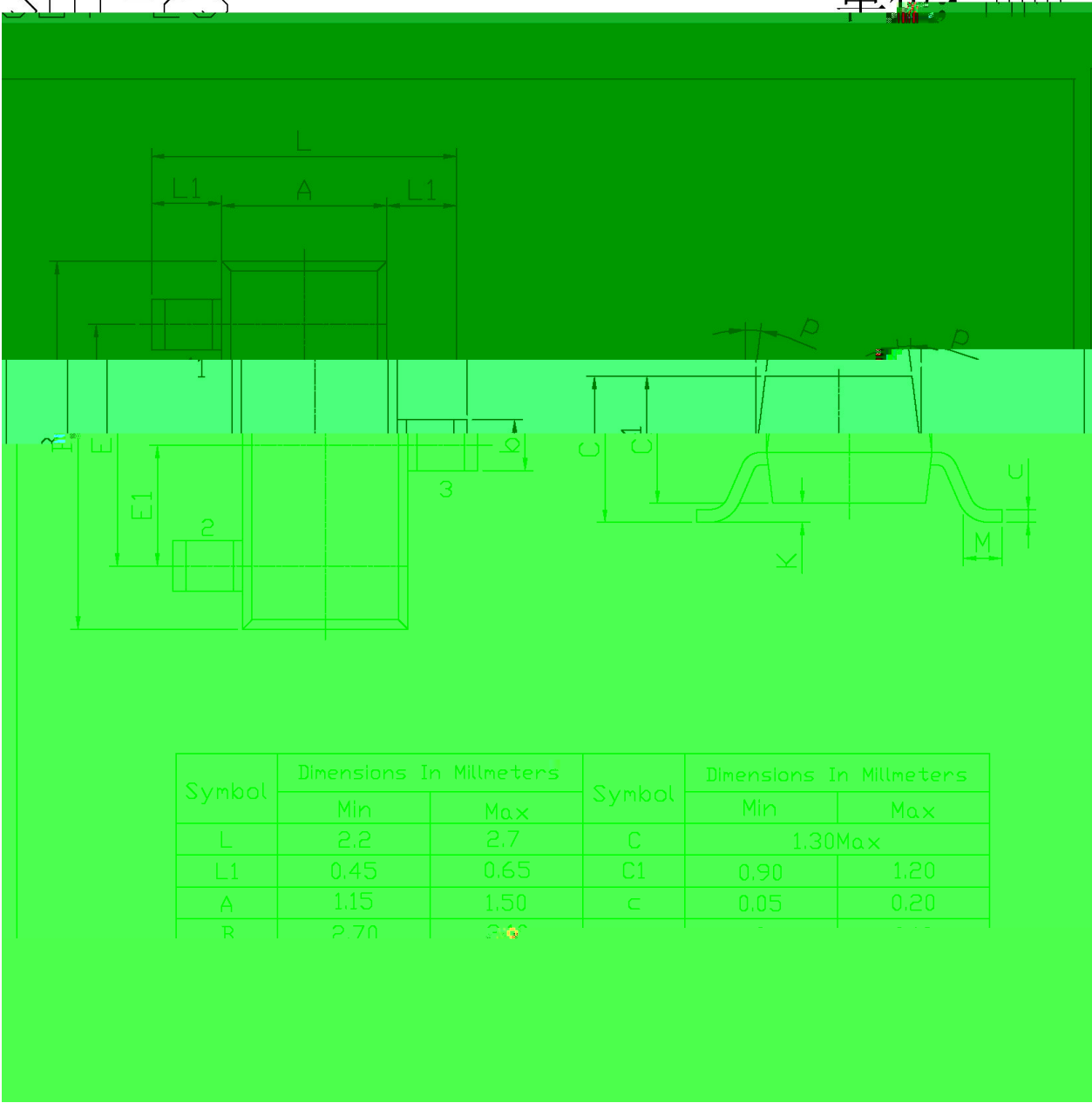
/ Electrical Characteristic Curve



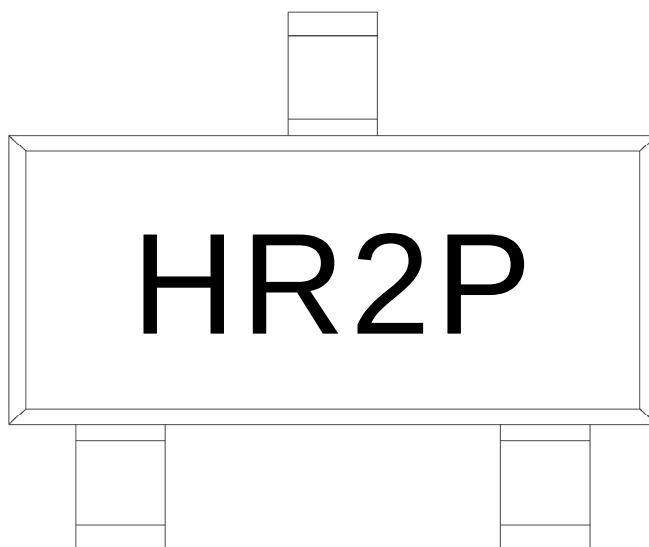
/ Package Dimensions

SOT-23

单位: mm



/ Marking Instructions



H

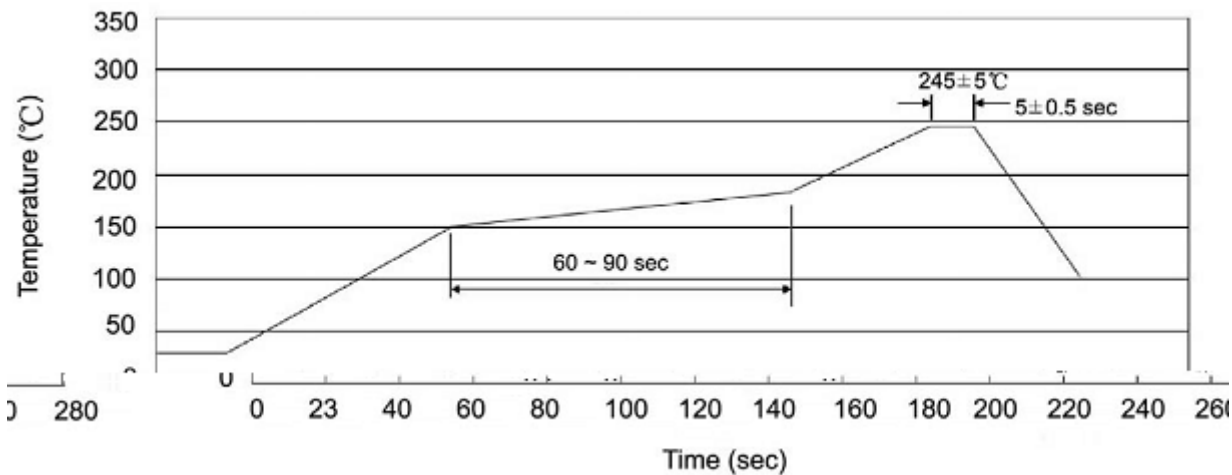
2RP

Note:

H: Company Code.

2RP: Product Type Code.

() / **Temperature Profile for IR Reflow Soldering(Pb-Free)**



Note:

- | | | | | | |
|---|-------|-----|-----------|---|--------------------------------------|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. | |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ **Resistance to Soldering Heat Test Conditions**

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ **Packaging SPEC.**

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205

/ **Notices**